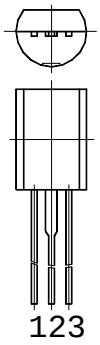
Transys Electronics LIMITED

TO-92MOD Plastic-Encapsulated Transistors

2SB740 TRANSISTOR (PNP)

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



FEATURE

Power dissipation

P_{CM}: 0.9 W (Tamb=25℃)

Collector current

I_{CM}: -1 A

Collector-base voltage

$V_{(BR)CBO}$: -70 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= -10μA , I_E=0	-70		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA , I_B=0	-50		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -10μA, I_C=0	-6		V
Collector cut-off current	I_{CBO}	V_{CB}= -55 V, I_E=0		-1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -6 V, I_C=0		-0.2	μA
DC current gain	h_{FE}	V_{CE}=-2 V, I_C= -100mA	100	320	
Collector-emitter saturation voltage	V_{CEsat}	I_C= -1A, I_B=-100mA		-0.6	V
Transition frequency	f_T	V_{CE}=-2V, I_C= -10mA	100		MHz
Output capacitance	C_{ob}	V_{CE}=-10V, I_E=0, f=1 MHz		45	pF

CLASSIFICATION OF h_{FE}

Rank	B	C
Range	100-200	160-320